

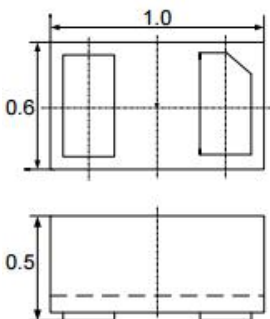
Description

The ESD12V08 is a bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The ESD12V08 has a low capacitance with a typical value at 8pF, and complies with the IEC 61000-4-2 (ESD) with $\pm 25\text{kV}$ air and $\pm 25\text{kV}$ contact discharge. It is assembled into an ultra-small 1.0x0.6x0.5mm lead-free DFN package. The small size, low capacitance and high ESD surge protection make ESD12V08 an ideal choice to protect cell phone, digital visual interfaces and other high speed ports.

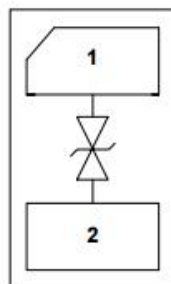
Features

- Ultra small package: 1.0x0.6x0.5mm
- Protects one data or power line
- Working voltage: 12V
- Ultra low capacitance: 8pF typical
- 2-pin leadless package
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 25\text{kV}$
 - Contact discharge: $\pm 25\text{kV}$
 - IEC61000-4-5 (Lightning) 8A (8/20us)
- RoHS Compliant

Dimensions & Symbol (Unit: mm Max)



Package Dimensions



Circuit and Pin Schematic

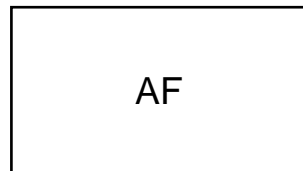
Mechanical Characteristics

- Package: DFN1006-2 (1.0×0.6×0.5mm)
- Case Material: “Green” Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Display Ports
- MDDI Ports
- USB Ports
- Digital Visual Interface (DVI)
- PCI Express and Serial SATA Ports

Marking Information



Ordering Information

Part Number	Packaging	Reel Size
ESD12V08	10000/Tape & Reel	7 inch

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$, RH=45%-75%, unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak Pulse Power (tp=8/20μs waveform)	P_{ppp}	180	W
Peak Pulse Current (8/20μs)	I_{pp}	8	A
ESD per IEC 61000-4-2 (Air)	VESD	±25	kV
ESD per IEC 61000-4-2 (Contact)		±25	
Operating Temperature Range	T_J	-55 to +125	°C
Storage Temperature Range	T_{stg}	-55 to +150	°C

Electrical Characteristics ($T_A=25^{\circ}\text{C}$)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			12	V	
Breakdown Voltage	V_{BR}	13		15	V	$I_T = 1\text{mA}$
Reverse Leakage Current	I_R			0.2	μA	$V_{RWM} = 12\text{V}$
Clamping Voltage	V_C		20	23	V	$I_{PP} = 8\text{A}$ (8 x 20μs pulse)
Junction Capacitance	C_J		8		pF	$V_R = 0\text{V}$, $f = 1\text{MHz}$

Typical Performance Characteristics (T_A=25°C unless otherwise Specified)

Figure 1: Peak Pulse Power vs. Pulse Time

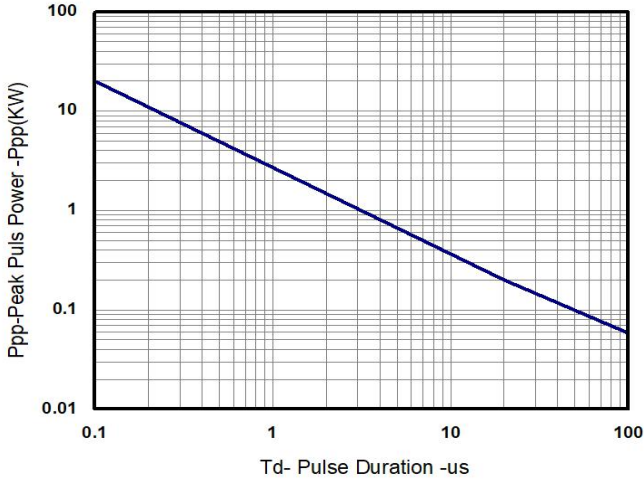


Figure 2: Power Derating Curve

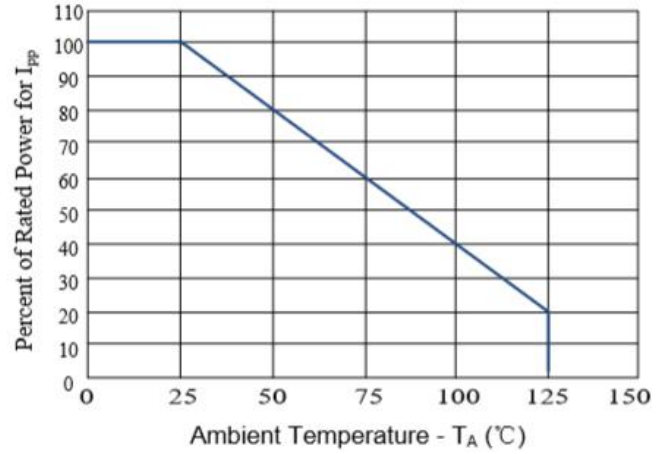


Figure 3: Clamping Voltage vs. Peak Pulse Current

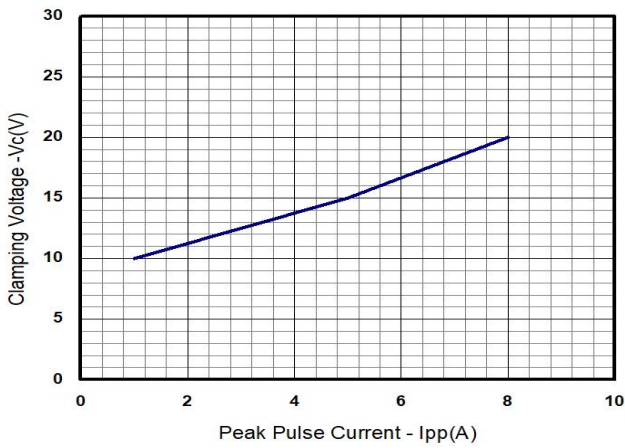


Figure 4: Normalized Junction Capacitance vs. Reverse Voltage

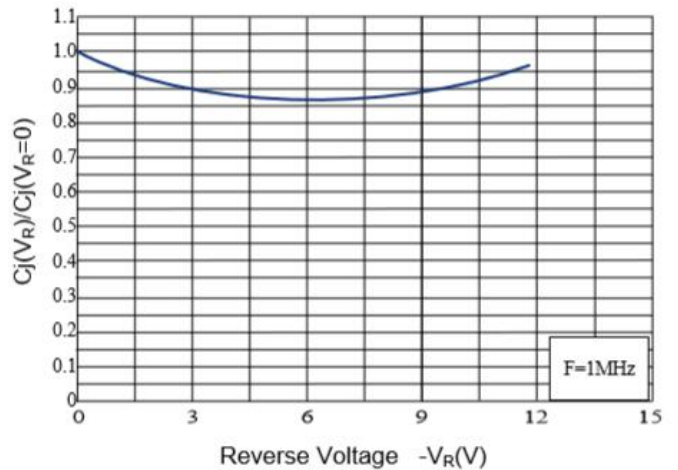
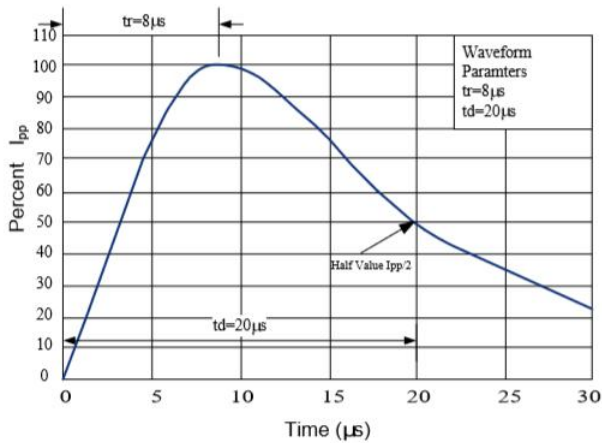
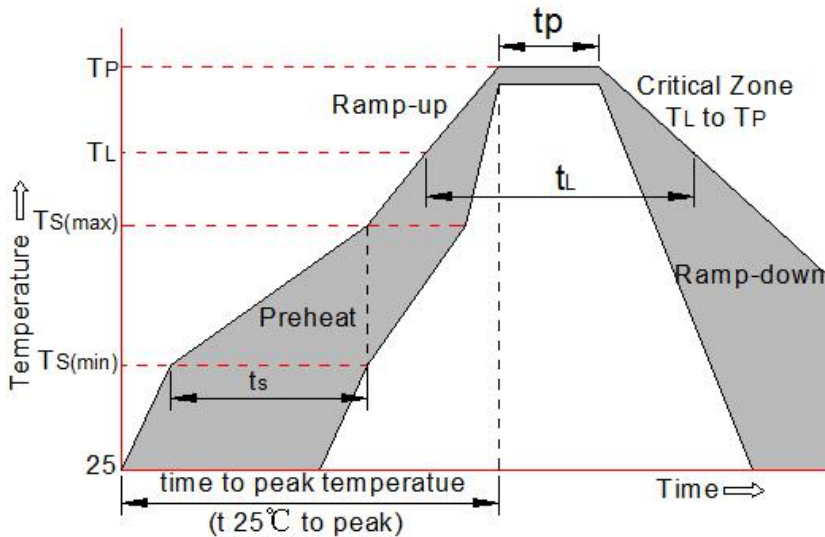


Figure 5: 8/20μs Pulse Waveform

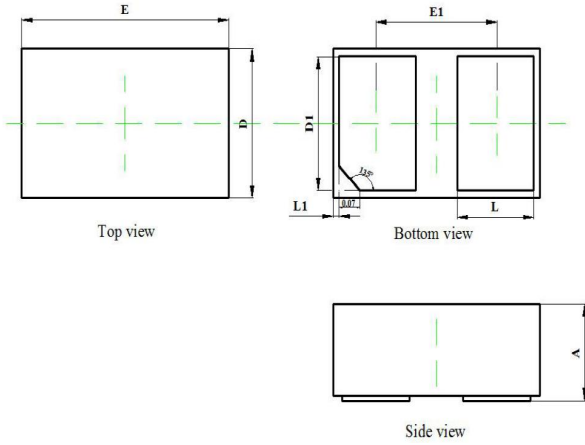


Soldering Parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (t_s)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L) (Liquid us)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_p)		8 min. Max
Do not exceed		+260°C

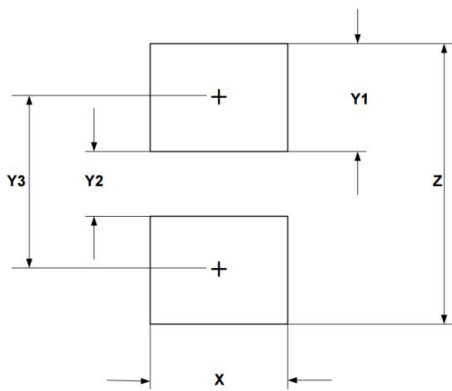


Package Mechanical Data



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.320	0.420	0.013	0.017
D	0.550	0.650	0.022	0.026
E	0.950	1.050	0.037	0.041
D1	0.450	0.550	0.018	0.022
E1	0.550	0.650	0.022	0.026
L	0.280	0.380	0.011	0.015
L1	0.000	0.100	0.000	0.004

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
X	0.60	0.024
Y1	0.50	0.020
Y2	0.30	0.012
Y3	0.80	0.032
Z	1.30	0.052